



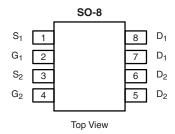
# Dual P-Channel 1.8-V (G-S) MOSFET

| PRODUCT SUMMARY     |                                    |                    |  |  |
|---------------------|------------------------------------|--------------------|--|--|
| V <sub>DS</sub> (V) | $R_{DS(on)}(\Omega)$               | I <sub>D</sub> (A) |  |  |
|                     | 0.021 at V <sub>GS</sub> = - 4.5 V | - 8.0              |  |  |
| - 8                 | 0.027 at V <sub>GS</sub> = - 2.5 V | - 7.0              |  |  |
|                     | 0.040 at V <sub>GS</sub> = - 1.8 V | - 5.8              |  |  |

#### **FEATURES**

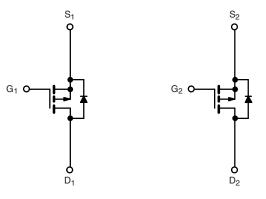
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFETs: 1.8 V Rated
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4965DY-T1-E3 (Lead (Pb)-free)

Si4965DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

P-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted |                        |                                   |             |      |  |
|---|------------------------|-----------------------------------|-------------|------|--|
| Parameter   |                        | Symbol                            | Limit       | Unit |  |
| Drain-Source Voltage  |                        | V <sub>DS</sub>                   | - 8         | V    |  |
| Gate-Source Voltage   |                        | V <sub>GS</sub>                   | ± 8         |      |  |
| Continuous Drain Current (T <sub>.J</sub> = 150 °C) <sup>a, b</sup>     | T <sub>A</sub> = 25 °C | I <sub>D</sub>                    | - 8.0       |      |  |
| Continuous Drain Current (1 <sub>J</sub> = 150 °C) <sup>2, 3</sup>      | T <sub>A</sub> = 70 °C |                                   | - 6.4       |      |  |
| Pulsed Drain Current  |                        | I <sub>DM</sub>                   | - 30        | - A  |  |
| Continuous Source Current (Diode Conduction) <sup>a, b</sup>            |                        | I <sub>S</sub>                    | - 1.7       |      |  |
| Maximum Power Dissipation <sup>a, b</sup>                               | T <sub>A</sub> = 25 °C | P <sub>D</sub>                    | 2.0         | w    |  |
|   | T <sub>A</sub> = 70 °C | ] 'D                              | 1.3         | VV   |  |
| Operating Junction and Storage Temperature Range                        |                        | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150 | °C   |  |

| THERMAL RESISTANCE RATINGS               |              |                   |         |         |      |  |
|--|--------------|-------------------|---------|---------|------|--|
| Parameter                                |              | Symbol            | Typical | Maximum | Unit |  |
|  | t ≤ 10 s     | D                 |         | 62.5    | °C/W |  |
| Maximum Junction-to-Ambient <sup>a</sup> | Steady State | R <sub>thJA</sub> | 93      |         | C/VV |  |

#### Notes:

a. Surface Mounted on FR4 board.

 $b.\ t \leq 10\ s.$ 

# Si4965DY

# Vishay Siliconix



| <b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted |                     |   |      |        |       |    |  |
|--|---------------------|---|------|--------|-------|----|--|
| Parameter  | Symbol              | Test Conditions Min. Typ.   |      | Max.   | Unit  |    |  |
| Static   |                     |   |      |        |       |    |  |
| Gate Threshold Voltage   | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$ - 0.45  |      |        | V     |    |  |
| Gate-Body Leakage  | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$  |      |        | ± 100 | nA |  |
| Zero Gate Voltage Drain Current                                      | I <sub>DSS</sub>    | $V_{DS} = -8 \text{ V}, V_{GS} = 0 \text{ V}$   | -1   |        | - 1   |    |  |
|  |                     | $V_{DS} = -8 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$                        |      |        | - 5   | μΑ |  |
| On-State Drain Current <sup>a</sup>                                  | I <sub>D(on)</sub>  | $V_{DS} \ge$ - 5 V, $V_{GS} =$ - 4.5 V  | - 20 |        |       | Α  |  |
|  |                     | $V_{GS} = -4.5 \text{ V}, I_D = -8.0 \text{ A}$   |      | 0.0175 | 0.021 |    |  |
| Drain-Source On-State Resistance <sup>a</sup>                        | R <sub>DS(on)</sub> | $V_{GS} = -2.5 \text{ V}, I_D = -7.0 \text{ A}$   |      | 0.022  | 0.027 | Ω  |  |
|  |                     | V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 5.8 A   |      | 0.031  | 0.040 |    |  |
| Forward Transconductance <sup>a</sup>                                | 9 <sub>fs</sub>     | $V_{DS} = -5 \text{ V}, I_{D} = -8.0 \text{ A}$   |      | 27     |       | S  |  |
| Diode Forward Voltage <sup>a</sup>                                   | $V_{SD}$            | $I_S = -1.7 \text{ A}, V_{GS} = 0 \text{ V}$  |      |        | - 1.2 | V  |  |
| Dynamic <sup>b</sup>   |                     |   |      |        |       |    |  |
| Total Gate Charge  | $Q_g$               |   |      | 36     | 55    |    |  |
| Gate-Source Charge   | $Q_{gs}$            | $V_{DS} = -4 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -8.0 \text{ A}$                          |      | 7.5    |       | nC |  |
| Gate-Drain Charge  | Q <sub>gd</sub>     |   |      | 5.0    |       |    |  |
| Turn-On Delay Time   | t <sub>d(on)</sub>  |   |      | 35     | 70    |    |  |
| Rise Time  | t <sub>r</sub>      | $V_{DD}$ = - 4 V, $R_L$ = 4 $\Omega$  |      | 45     | 90    |    |  |
| Turn-Off Delay Time  | t <sub>d(off)</sub> | $\text{I}_\text{D}\cong$ - 1 A, $\text{V}_\text{GEN}$ = - 4.5 V, $\text{R}_\text{g}$ = 6 $\Omega$ |      | 170    | 340   | ns |  |
| Fall Time  | t <sub>f</sub>      |   |      | 90     | 180   |    |  |
| Source-Drain Reverse Recovery Time                                   | t <sub>rr</sub>     | I <sub>F</sub> = - 1.7 A, dl/dt = 100 A/μs  |      | 60     | 90    |    |  |

#### Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

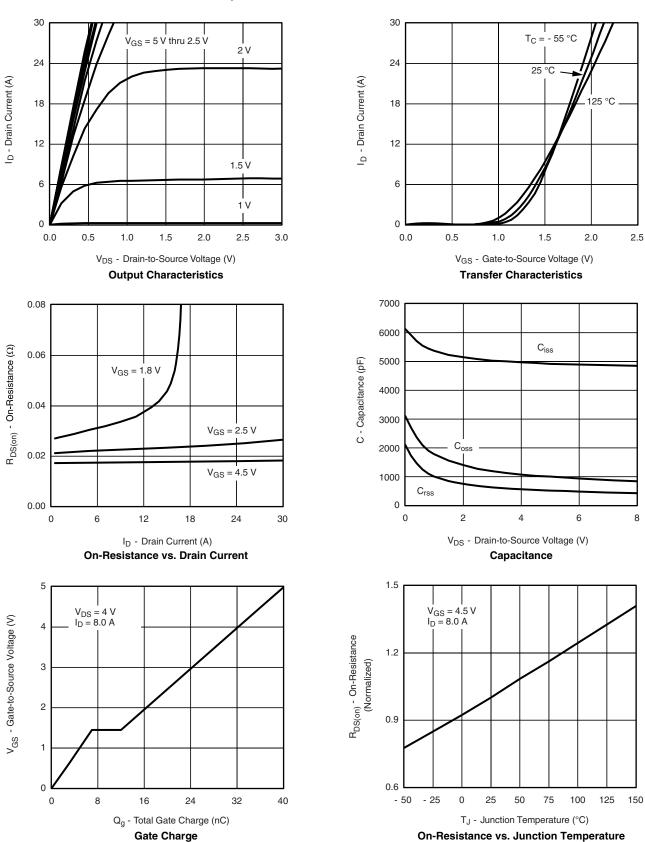
a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.





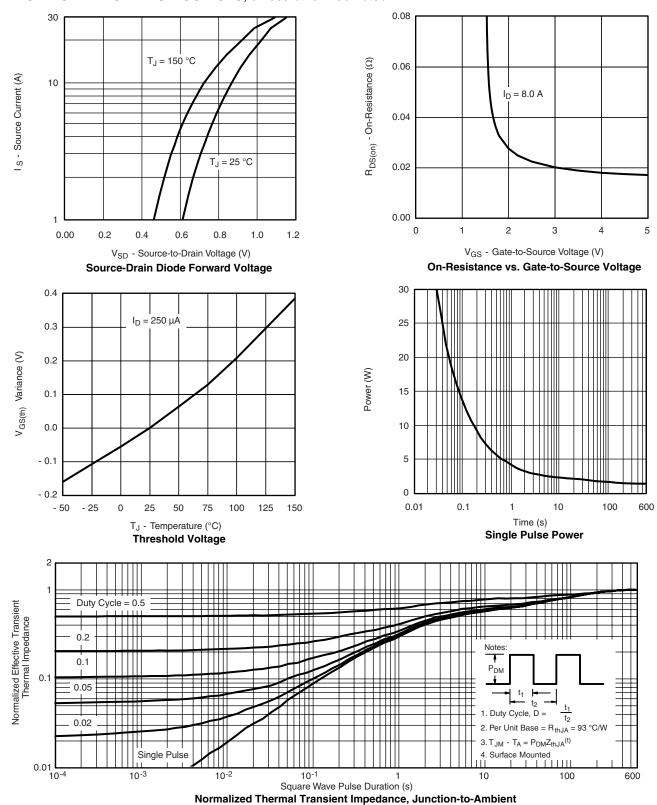
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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